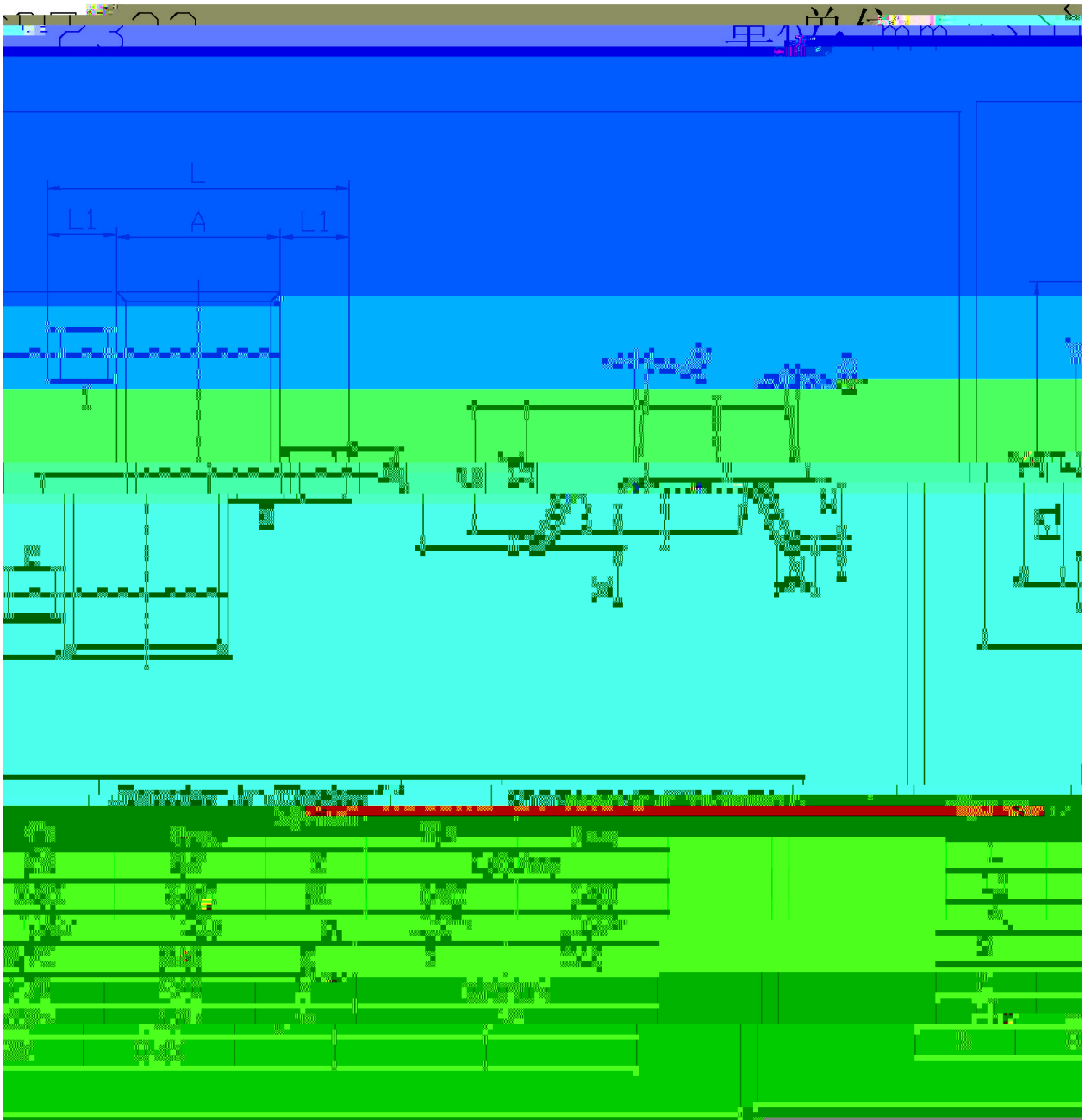
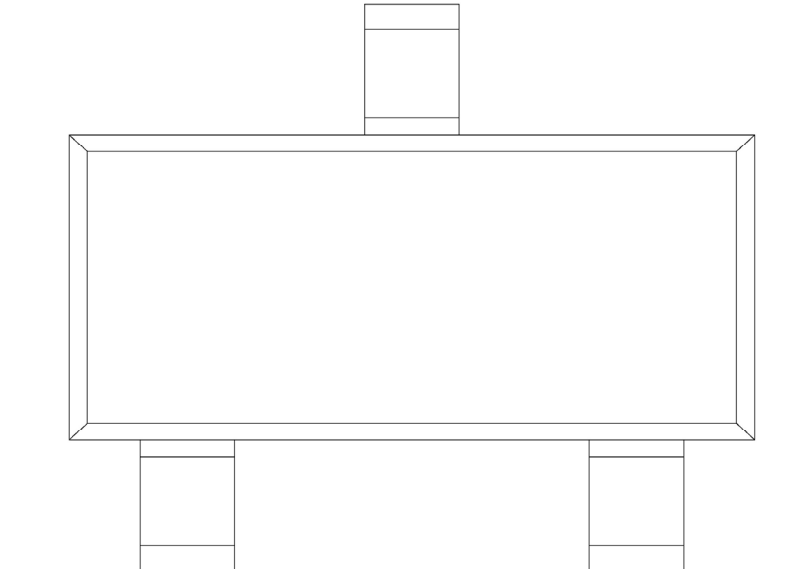


Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	3.0	V
Collector Current	I_C	15	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

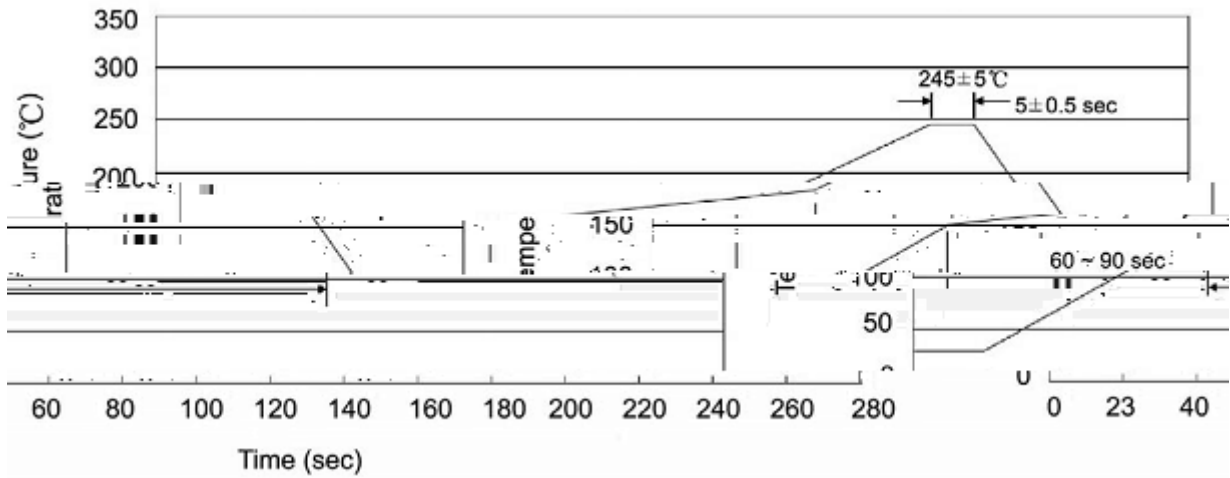
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- Base Breakdown Voltage	V_{CBO}	$I_C=10\mu A$	30			V
Emitter-Base Breakdown Voltage	V_{EBO}	$I_E=10\mu A$	3.0			V
DC Current Gain	h_{FE}	$V_{CE}=6.0V$ $I_C=1.0mA$	40		260	
Transition Frequency	f_T	$V_{CB}=6.0V$ $I_C=1.0mA$	450	650		MHz
Base to Emitter Voltage	V_{BE}	$V_{CB}=6.0V$ $I_C=1.0mA$		0.72		V
Common Emitter Reverse Transfer Capacitance	C_{re}	$V_{CB}=6.0V$ $I_C=1.0mA$ $f=10.7MHz$		0.8	1.0	PF
Power Gain	P_G	$V_{CB}=6.0V$ $I_C=1.0mA$ $f=100MHz$		24		dB
Noise Figure	NF	$V_{CB}=6.0V$ $I_C=1.0mA$ $f=100MHz$		3.3		dB







Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | |
|---|--------|------------|---|
| 1 | 25 150 | 60 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245..5 | 5..0.5sec; | 2.Peak Temp.:245..5 , Duration:5..0.5sec. |
| 3 | 2 10 | /sec. | 3. |